



MRF6P9220HR3 replaced by MRFE6P9220HR3. Refer to Device Migration PCN12895 for more details.

RF Power Field Effect Transistor

N-Channel Enhancement-Mode Lateral MOSFET

Designed for broadband commercial and industrial applications with frequencies up to 1000 MHz. The high gain and broadband performance of these devices make them ideal for large-signal, common-source amplifier applications in 28 volt base station equipment.

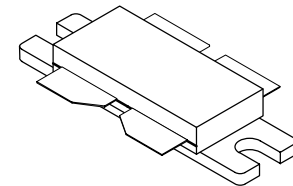
- Typical Single-Carrier N-CDMA Performance @ 880 MHz: $V_{DD} = 28$ Volts, $I_{DQ} = 1600$ mA, $P_{out} = 47$ Watts Avg., IS-95 CDMA (Pilot, Sync, Paging, Traffic Codes 8 Through 13). Channel Bandwidth = 1.2288 MHz. PAR = 9.8 dB @ 0.01% Probability on CCDF.
 Power Gain — 20 dB
 Drain Efficiency — 30%
 ACPR @ 750 kHz Offset — -47.1 dBc in 30 kHz Bandwidth
- Capable of Handling 10:1 VSWR, @ 28 Vdc, 880 MHz, 220 Watts CW Output Power

Features

- Characterized with Series Equivalent Large-Signal Impedance Parameters
- Internally Matched for Ease of Use
- Device Designed for Push-Pull Operation Only
- Qualified Up to a Maximum of 32 V_{DD} Operation
- Integrated ESD Protection
- Designed for Lower Memory Effects and Wide Instantaneous Bandwidth Applications
- RoHS Compliant
- In Tape and Reel. R3 Suffix = 250 Units per 56 mm, 13 inch Reel.

MRF6P9220HR3

**880 MHz, 47 W AVG., 28 V
 SINGLE N-CDMA
 LATERAL N-CHANNEL
 RF POWER MOSFET**



**CASE 375G-04, STYLE 1
 NI-860C3**

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Table 1. Maximum Ratings

Rating	Symbol	Value	Unit
Drain-Source Voltage	V_{DSS}	-0.5, +68	Vdc
Gate-Source Voltage	V_{GS}	-0.5, +12	Vdc
Storage Temperature Range	T_{stg}	-65 to +150	°C
Case Operating Temperature	T_C	150	°C
Operating Junction Temperature (1,2)	T_J	225	°C

Table 2. Thermal Characteristics

Characteristic	Symbol	Value (2,3)	Unit
Thermal Resistance, Junction to Case Case Temperature 80°C, 220 W CW Case Temperature 76°C, 47 W CW	$R_{\theta JC}$	0.25 0.28	°C/W

1. Continuous use at maximum temperature will affect MTTF.
2. MTTF calculator available at <http://www.freescale.com/rf>. Select Software & Tools/Development Tools/Calculators to access MTTF calculators by product.
3. Refer to AN1955, *Thermal Measurement Methodology of RF Power Amplifiers*. Go to <http://www.freescale.com/rf>. Select Documentation/Application Notes - AN1955.

Table 3. ESD Protection Characteristics

Test Methodology	Class
Human Body Model (per JESD22-A114)	3B (Minimum)
Machine Model (per EIA/JESD22-A115)	C (Minimum)
Charge Device Model (per JESD22-C101)	IV (Minimum)

Table 4. Electrical Characteristics ($T_C = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
Off Characteristics ⁽¹⁾					
Zero Gate Voltage Drain Leakage Current ⁽⁴⁾ ($V_{DS} = 68\text{ Vdc}$, $V_{GS} = 0\text{ Vdc}$)	I_{DSS}	—	—	10	μAdc
Zero Gate Voltage Drain Leakage Current ⁽⁴⁾ ($V_{DS} = 28\text{ Vdc}$, $V_{GS} = 0\text{ Vdc}$)	I_{DSS}	—	—	1	μAdc
Gate-Source Leakage Current ($V_{GS} = 5\text{ Vdc}$, $V_{DS} = 0\text{ Vdc}$)	I_{GSS}	—	—	1	μAdc

On Characteristics

Gate Threshold Voltage ⁽¹⁾ ($V_{DS} = 10\text{ Vdc}$, $I_D = 350\ \mu\text{Adc}$)	$V_{GS(th)}$	1	2.2	3	Vdc
Gate Quiescent Voltage ⁽³⁾ ($V_{DD} = 28\text{ Vdc}$, $I_D = 1600\text{ mAdc}$, Measured in Functional Test)	$V_{GS(Q)}$	2	2.8	4	Vdc
Drain-Source On-Voltage ⁽¹⁾ ($V_{GS} = 10\text{ Vdc}$, $I_D = 2.4\text{ Adc}$)	$V_{DS(on)}$	0.1	0.22	0.3	Vdc

Dynamic Characteristics ^(1,2)

Reverse Transfer Capacitance ($V_{DS} = 28\text{ Vdc} \pm 30\text{ mV(rms)ac}$ @ 1 MHz, $V_{GS} = 0\text{ Vdc}$)	C_{rss}	—	2.1	—	pF
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Functional Tests ⁽³⁾ (In Freescale Test Fixture, 50 ohm system) $V_{DD} = 28\text{ Vdc}$, $I_{DQ} = 1600\text{ mA}$, $P_{out} = 47\text{ W Avg. N-CDMA}$, $f = 880\text{ MHz}$, Single-Carrier N-CDMA, 1.2288 MHz Channel Bandwidth Carrier. ACPR measured in 30 kHz Channel Bandwidth @ $\pm 750\text{ kHz}$ Offset. PAR = 9.8 dB @ 0.01% Probability on CCDF.

Power Gain	G_{ps}	18.5	20	23	dB
Drain Efficiency	η_D	28.5	30	—	%
Adjacent Channel Power Ratio	ACPR	—	-47.1	-45	dBc
Input Return Loss	IRL	—	-14	-9	dB

1. Each side of device measured separately.
2. Part internally matched both on input and output.
3. Measurement made with device in push-pull configuration.
4. Drains are tied together internally as this is a total device value.

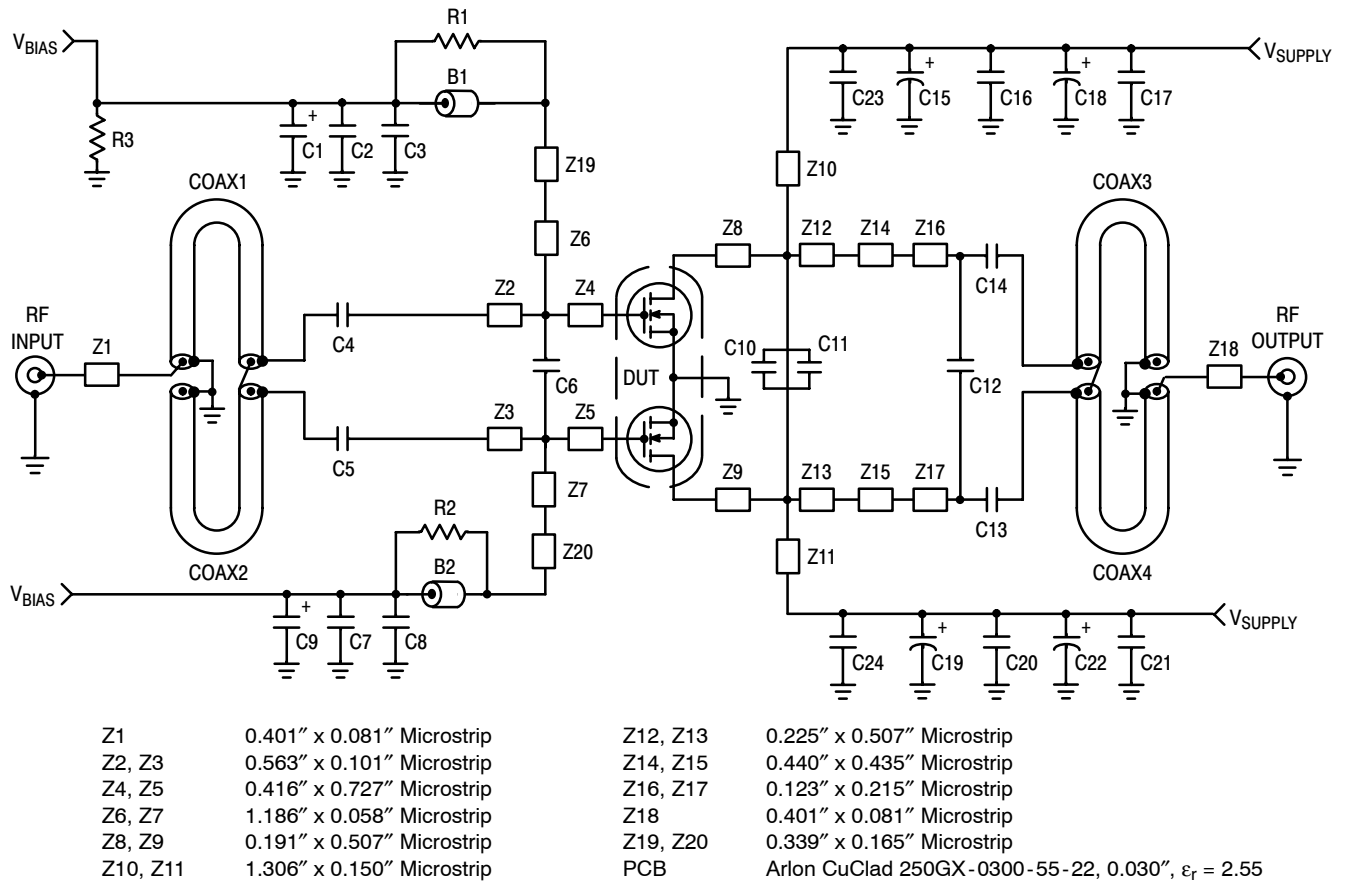


Figure 1. MRF6P9220HR3 Test Circuit Schematic

Table 5. MRF6P9220HR3 Test Circuit Component Designations and Values

Part	Description	Part Number	Manufacturer
B1, B2	Ferrite Beads, Short	2743019447	Fair-Rite
C1, C9	1.0 μ F, 50 V Tantalum Chip Capacitors	T491C105K050AT	Kemet
C2, C7, C17, C21	0.1 μ F Chip Capacitors	CDR33BX104AKWT	Kemet
C3, C8, C16, C20	1000 pF Chip Capacitors	ATC100B102JT50XT	ATC
C4, C5, C13, C14	100 pF Chip Capacitors	ATC100B101JT500XT	ATC
C6, C12	8.2 pF Chip Capacitors	ATC100B8R2BT500XT	ATC
C10	9.1 pF Chip Capacitor	ATC100B9R1BT500XT	ATC
C11	1.8 pF Chip Capacitor	ATC100B1R8BT500XT	ATC
C15, C19	47 μ F, 50 V Electrolytic Capacitors	EMVY500ADA470MF80G	Nippon Chemi-Con
C18, C22	470 μ F, 63 V Electrolytic Capacitors	EMVY630GTR471MLN0S	Nippon Chemi-Con
C23, C24	22 pF Chip Capacitors	ATC100B220FT500XT	ATC
Coax1, 2, 3, 4	50 Ω , Semi Rigid Coax, 2.40" Long	UT-141A-TP	Micro-Coax
R1, R2	10 Ω , 1/4 W Chip Resistors	CRCW120610R0FKEA	Vishay
R3	1.0 k Ω , 1/4 W Chip Resistor	CRCW12061001FKEA	Vishay

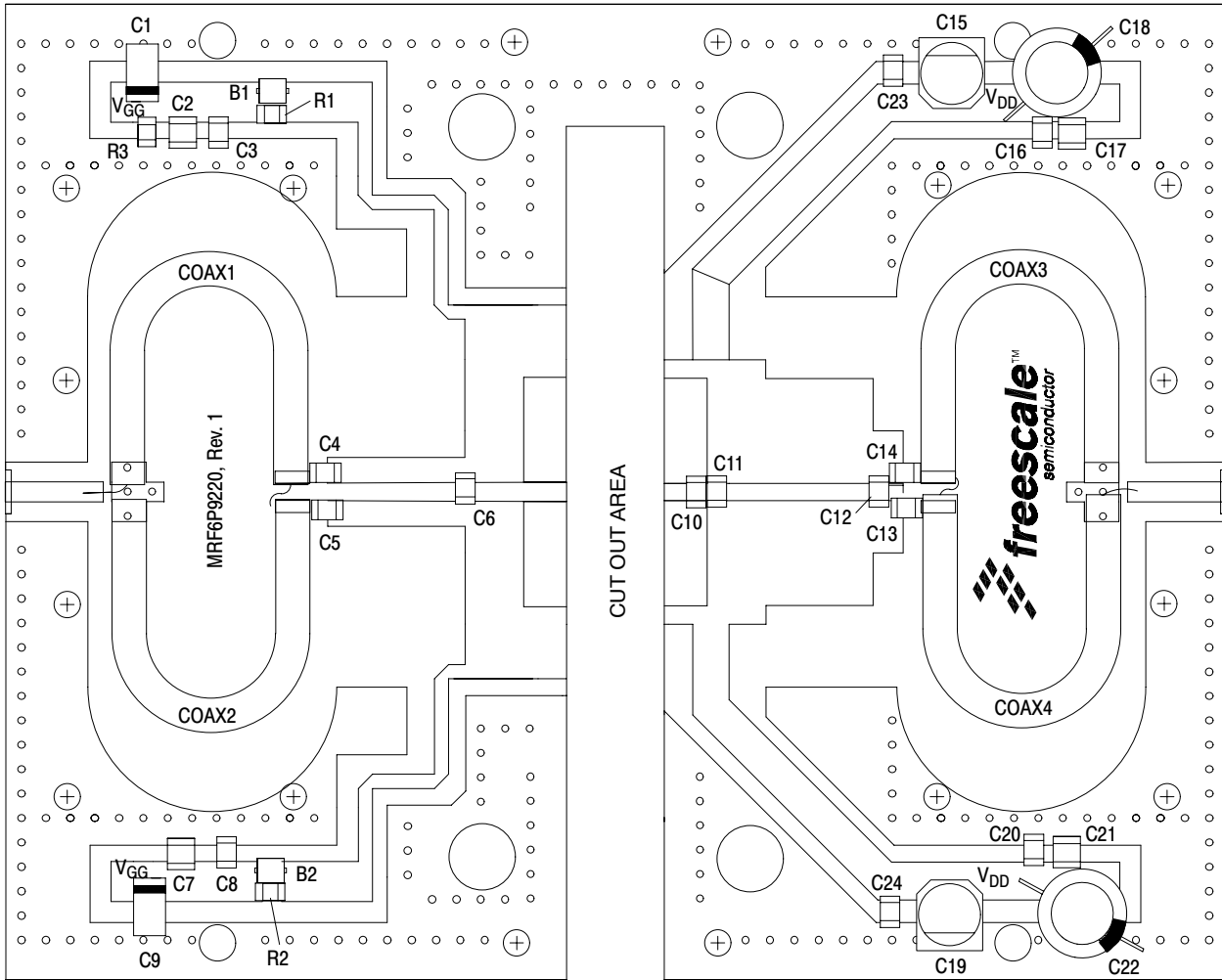


Figure 2. MRF6P9220HR3 Test Circuit Component Layout

TYPICAL CHARACTERISTICS

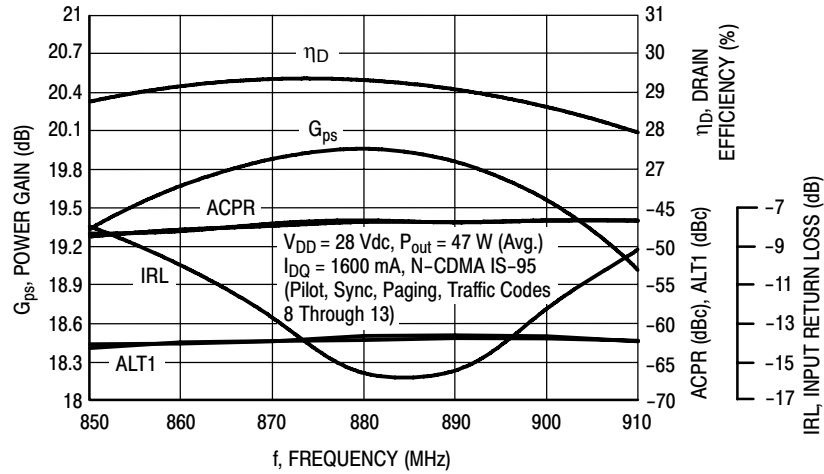


Figure 3. Single-Carrier N-CDMA Broadband Performance @ P_{out} = 47 Watts Avg.

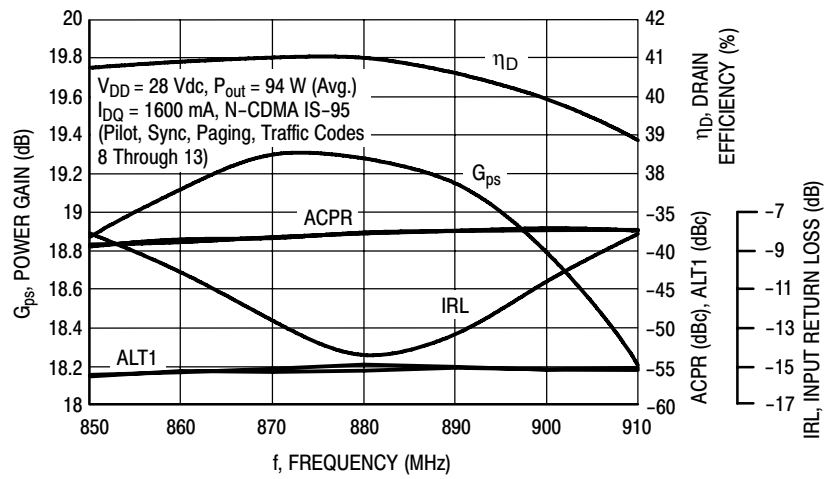


Figure 4. Single-Carrier N-CDMA Broadband Performance @ P_{out} = 94 Watts Avg.

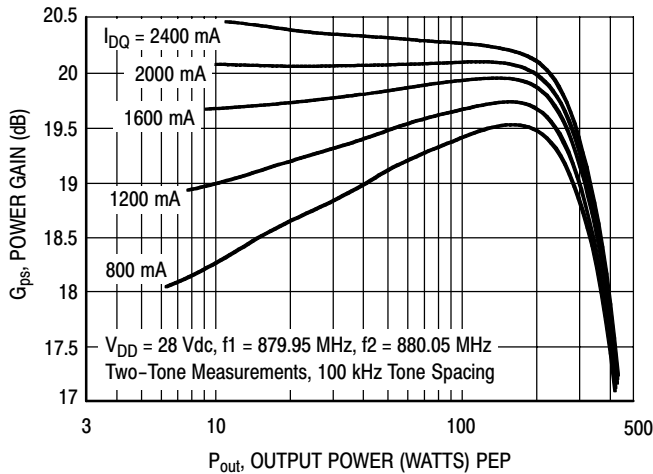


Figure 5. Two-Tone Power Gain versus Output Power

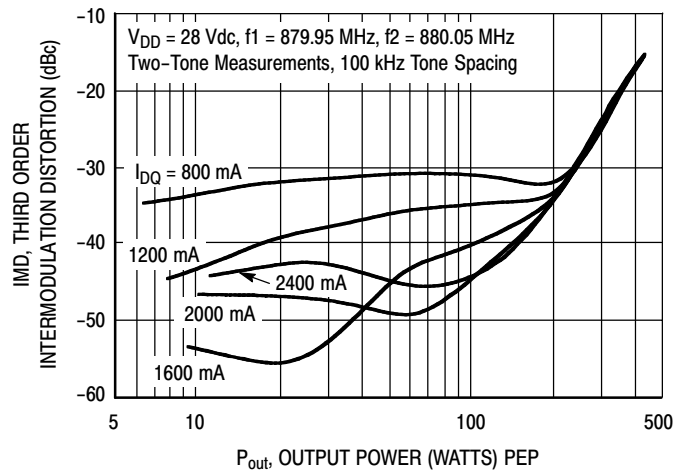


Figure 6. Third Order Intermodulation Distortion versus Output Power

TYPICAL CHARACTERISTICS

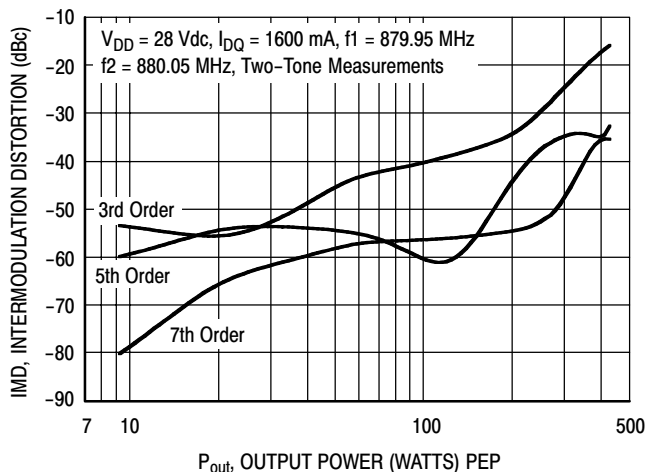


Figure 7. Intermodulation Distortion Products versus Output Power

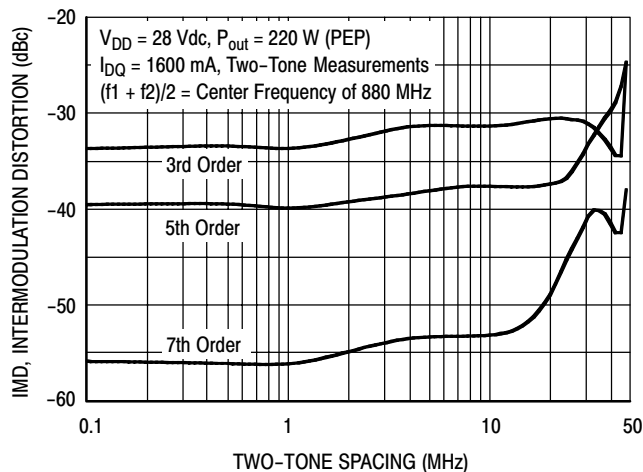


Figure 8. Intermodulation Distortion Products versus Tone Spacing

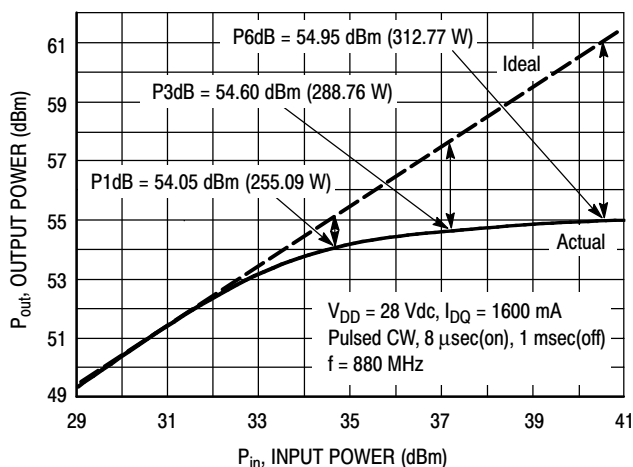


Figure 9. Pulsed CW Output Power versus Input Power

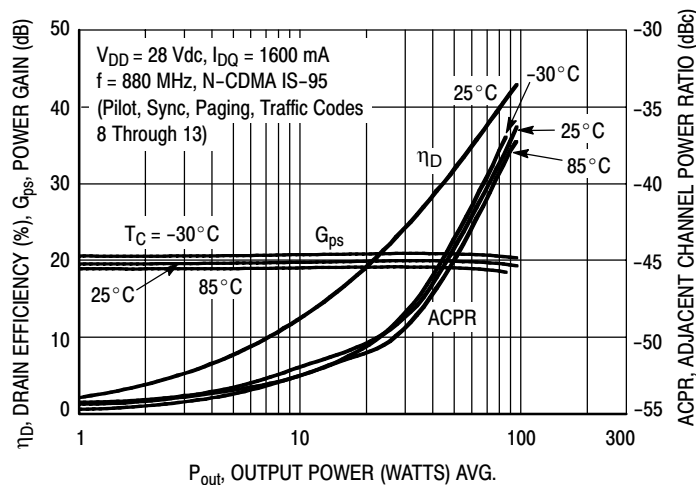


Figure 10. Single-Carrier N-CDMA ACPR, Power Gain and Drain Efficiency versus Output Power

TYPICAL CHARACTERISTICS

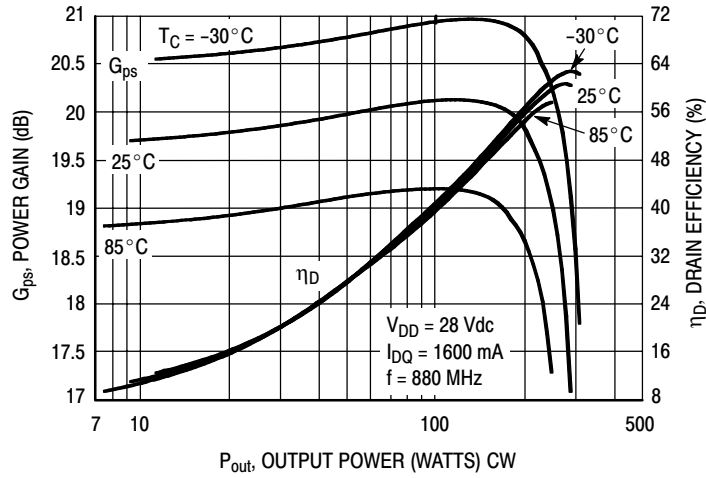


Figure 11. Power Gain and Drain Efficiency versus CW Output Power

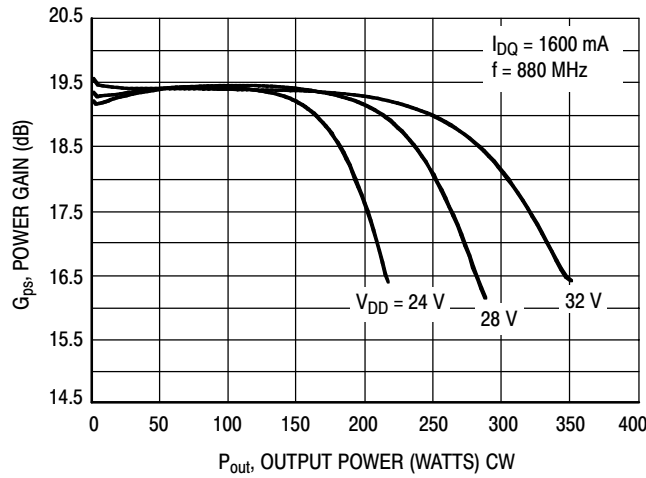
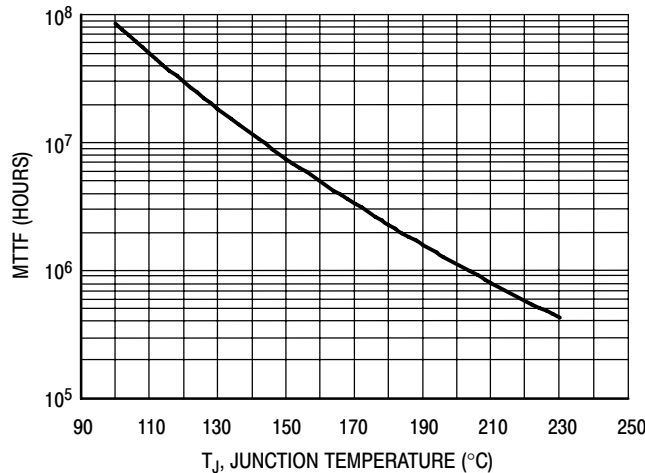


Figure 12. Power Gain versus Output Power



This above graph displays calculated MTTF in hours when the device is operated at $V_{DD} = 28$ Vdc, $P_{out} = 47$ W Avg., and $\eta_D = 30\%$.

MTTF calculator available at <http://www.freescale.com/rf>. Select Software & Tools/Development Tools/Calculators to access MTTF calculators by product.

Figure 13. MTTF Factor versus Junction Temperature

N-CDMA TEST SIGNAL

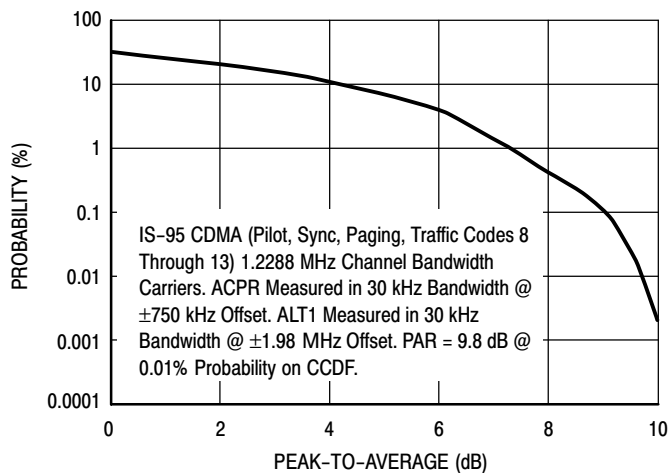


Figure 14. Single-Carrier CCDF N-CDMA

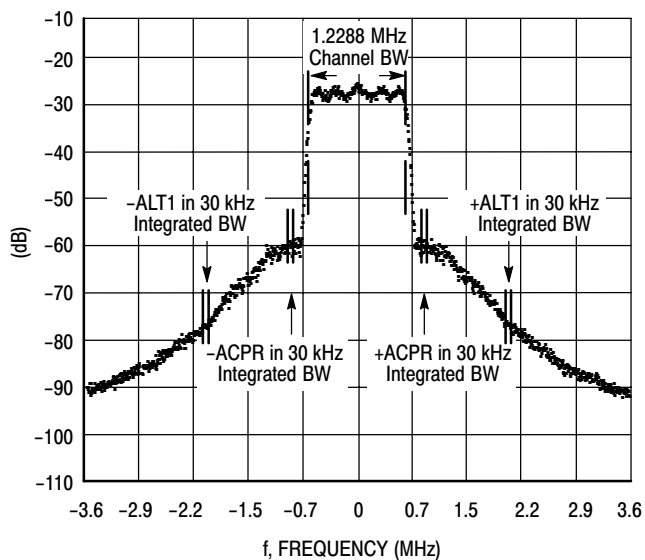
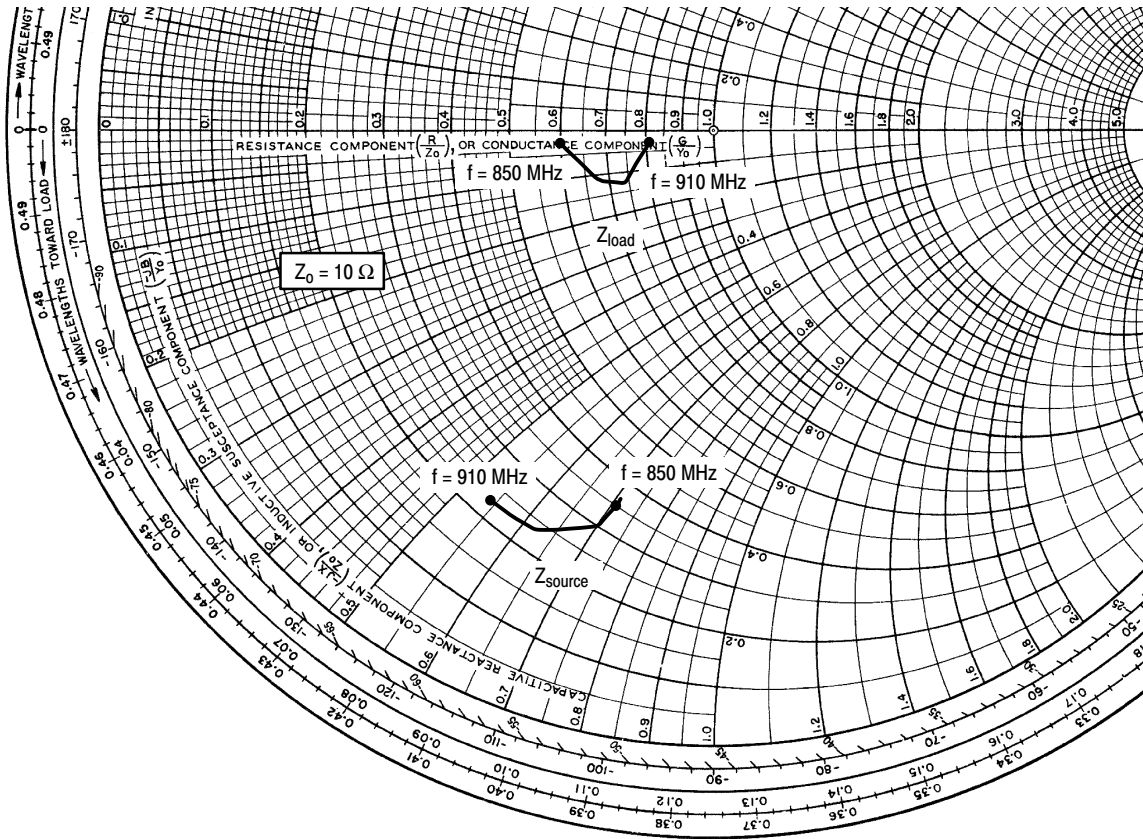


Figure 15. Single-Carrier N-CDMA Spectrum

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$V_{DD} = 28 \text{ Vdc}$, $I_{DQ} = 1600 \text{ mA}$, $P_{out} = 47 \text{ W Avg.}$

f MHz	Z_{source} Ω	Z_{load} Ω
850	$3.50 - j7.10$	$6.04 - j0.49$
865	$3.59 - j7.07$	$6.83 - j1.14$
880	$3.03 - j6.98$	$7.41 - j1.19$
895	$2.42 - j6.20$	$7.60 - j0.98$
910	$2.26 - j5.39$	$8.06 - j0.45$

Z_{source} = Test circuit impedance as measured from gate to gate, balanced configuration.

Z_{load} = Test circuit impedance as measured from drain to drain, balanced configuration.

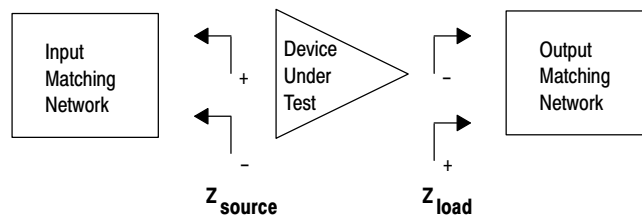
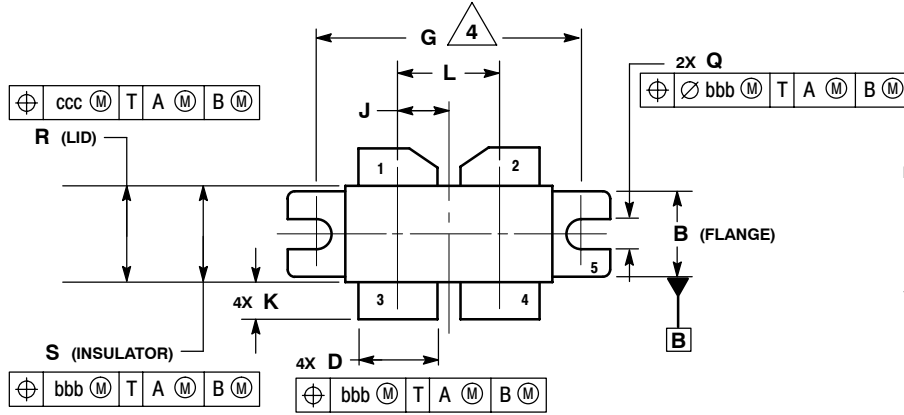


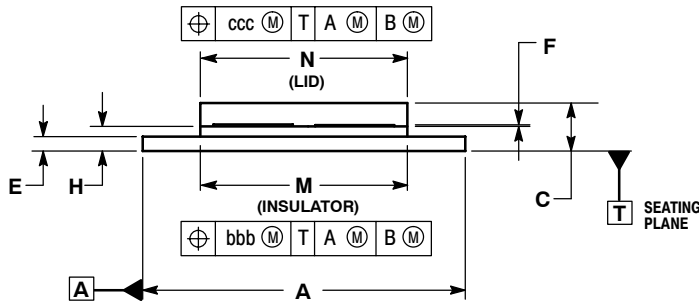
Figure 16. Series Equivalent Source and Load Impedance

PACKAGE DIMENSIONS



- NOTES:
 1. CONTROLLING DIMENSION: INCH.
 2. INTERPRET DIMENSIONS AND TOLERANCES PER ASME Y14.5M-1994.
 3. DIMENSION H TO BE MEASURED 0.030 (0.762) AWAY FROM PACKAGE BODY.
 4. RECOMMENDED BOLT CENTER DIMENSION OF 1.140 (28.96) BASED ON 3M SCREW.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	1.335	1.345	33.91	34.16
B	0.380	0.390	9.65	9.91
C	0.180	0.224	4.57	5.69
D	0.325	0.335	8.26	8.51
E	0.060	0.070	1.52	1.78
F	0.004	0.006	0.10	0.15
G	1.100 BSC		27.94 BSC	
H	0.097	0.107	2.46	2.72
J	0.2125 BSC		5.397 BSC	
K	0.135	0.165	3.43	4.19
L	0.425 BSC		10.8 BSC	
M	0.852	0.868	21.64	22.05
N	0.851	0.869	21.62	22.07
Q	0.118	0.138	3.00	3.30
R	0.395	0.405	10.03	10.29
S	0.394	0.406	10.01	10.31
bbb	0.010 REF		0.25 REF	
ccc	0.015 REF		0.38 REF	



- STYLE 1:
 PIN 1: DRAIN
 2: DRAIN
 3: GATE
 4: GATE
 5: SOURCE

**CASE 375G-04
 ISSUE G
 NI-860C3**

PRODUCT DOCUMENTATION

Refer to the following documents to aid your design process.

Application Notes

- AN1955: Thermal Measurement Methodology of RF Power Amplifiers

Engineering Bulletins

- EB212: Using Data Sheet Impedances for RF LDMOS Devices

REVISION HISTORY

The following table summarizes revisions to this document.

Revision	Date	Description
3	Aug. 2008	<ul style="list-style-type: none">• Listed replacement part and Device Migration notification reference number, p. 1• Removed Lower Thermal Resistance and Low Gold Plating bullets from Features section as functionality is standard, p. 1• Removed Total Device Dissipation from Max Ratings table as data was redundant (information already provided in Thermal Characteristics table), p. 1• Operating Junction Temperature increased from 200°C to 225°C in Maximum Ratings table and related "Continuous use at maximum temperature will affect MTTF" footnote added, p. 1• Corrected V_{DS} to V_{DD} in the RF test condition voltage callout for $V_{GS(Q)}$, On Characteristics table, p. 2• Removed Forward Transconductance from On Characteristics table as it no longer provided usable information, p. 2• Updated PCB information to show more specific material details, Fig. 1, Test Circuit Schematic, p. 3• Updated Part Numbers in Table 5, Component Designations and Values, to latest RoHS compliant part numbers, p. 3• Adjusted scale for Fig. 8, Intermodulation Distortion Products versus Tone Spacing, to show wider dynamic range, p. 6• Removed lower voltage tests from Fig. 12, Power Gain versus Output Power, due to fixed tuned fixture limitations, p. 7• Replaced Fig. 13, MTTF versus Junction Temperature with updated graph. Removed Amps² and listed operating characteristics and location of MTTF calculator for device, p. 7• Added Product Documentation and Revision History, p. 11
3.1	Dec. 2008	<ul style="list-style-type: none">• Fig. 1, Test Circuit Schematic, Z-list, changed Z6, Z7 from 0.058" x 1.01" Microstrip to 1.186" x 0.058" Microstrip; Z10, Z11 from 1.054" x 0.150" Microstrip to 1.306" x 0.150" Microstrip; and Z19, Z20 from 0.165" x 0.339" Microstrip to 0.339" x 0.165" Microstrip; also separated Z1 and Z18 into two lines in Z-list, p. 3• Table 5, Test Circuit Component Designations and Values, changed part numbers ATC100B102JP50XT to ATC100B102JT50XT and ATC100B101JP500XT to ATC100B101JT500XT, p. 3

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